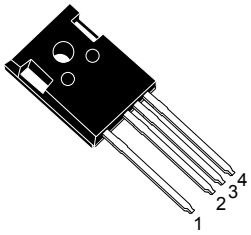
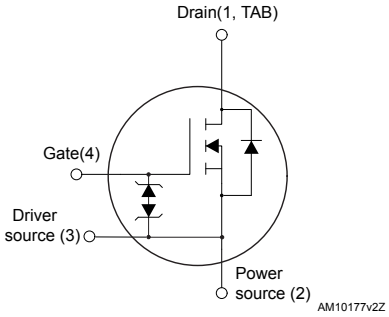
STW56N60M2-4

Datasheet

N-channel 600 V, 45 mΩ typ., 52 A MDmesh M2 Power MOSFET in a TO-247-4 package



TO247-4



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STW56N60M2-4	600 V	55 mΩ	52 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected
- Excellent switching performance thanks to the extra driving source pin

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Product status link
STW56N60M2-4

Product summary	
Order code	STW56N60M2-4
Marking	56N60M2
Package	TO-247-4
Packing	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	52	A
	Drain current (continuous) at T_C = 100 °C	33	
I_{DM}(1)	Drain current (pulsed)	208	A
P_{TOT}	Total power dissipation at T_C = 25 °C	350	W
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Maximum operating junction temperature	150	°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 52 A, di/dt = 400 A/µs, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 400 V.*
3. *V_{DD} ≤ 480 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.36	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max.)	7.5	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	1.1	J

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2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ± 25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 26 A		45	55	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	3750	-	pF
C_{oss}	Output capacitance		-	175	-	pF
C_{rss}	Reverse transfer capacitance		-	6.6	-	pF
$C_{o(er)}$ (1)	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 to 480 V	-	740	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz, open drain	-	4.7	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 52 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	91	-	nC
Q_{gs}	Gate-source charge		-	13.5	-	nC
Q_{gd}	Gate-drain charge		-	41	-	nC

1. *Coss eq. is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 26 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Switching times test circuit for resistive load and Figure 18. Switching time waveform)	-	18	-	ns
t_r	Rise time		-	26.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	119	-	ns
t_f	Fall time		-	14	-	ns

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Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		52	A
I_{SDM}(1)	Source-drain current (pulsed)		-		208	A
V_{SD}(2)	Forward on voltage	I_{SD} = 52 A, V_{GS} = 0	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 52 A, di/dt = 100 A/µs	-	496		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V	-	10		µC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	41		A
t_{rr}	Reverse recovery time	I_{SD} = 52 A, di/dt = 100 A/µs	-	632		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V, T_J = 150 °C	-	14		µC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	45		A

1. *Pulse width limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

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2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

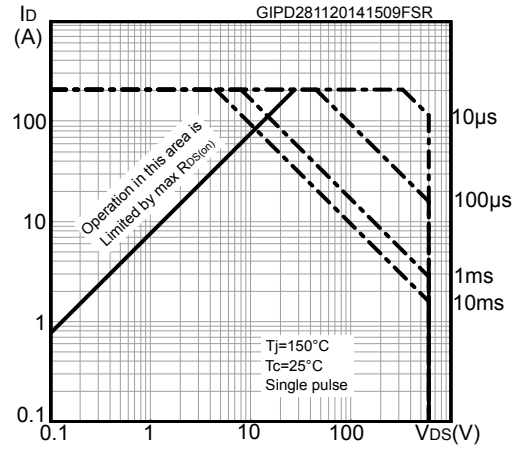


Figure 2. Thermal impedance

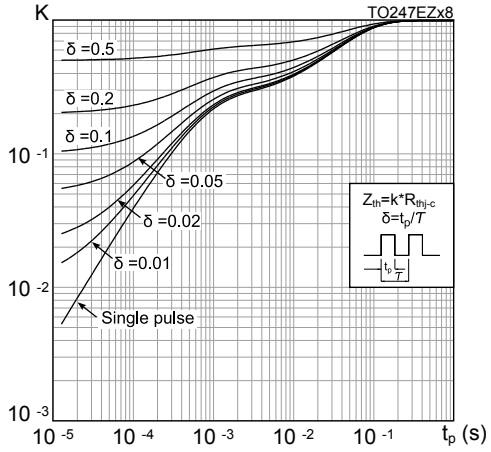


Figure 3. Output characteristics

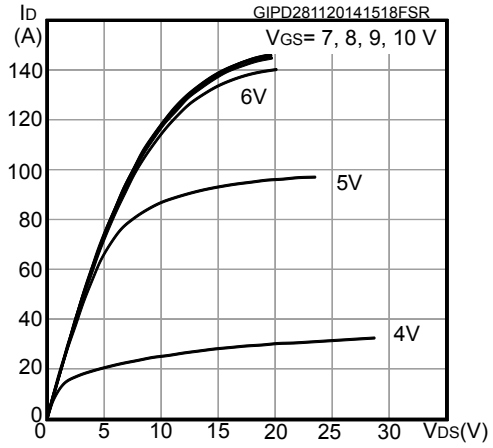


Figure 4. Transfer characteristics

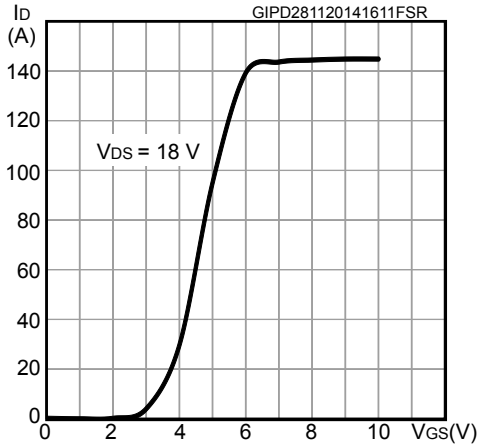


Figure 5. Gate charge vs gate-source voltage

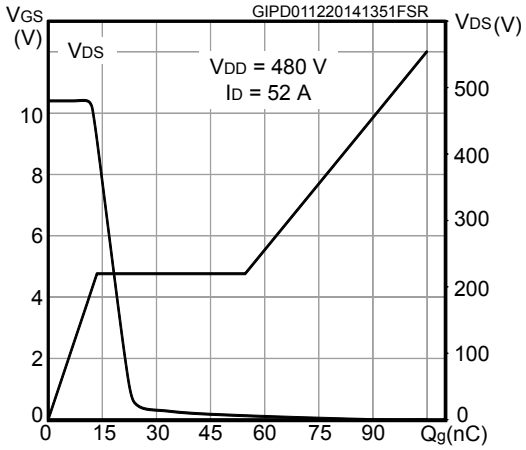
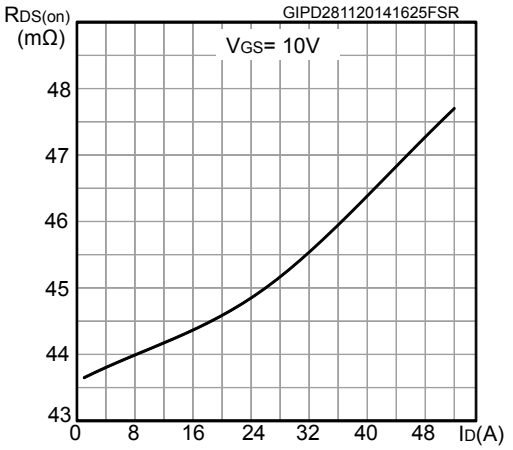


Figure 6. Static drain-source on-resistance



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Figure 7. Capacitance variations

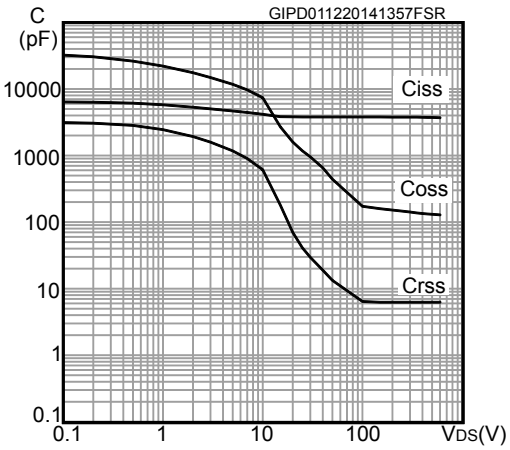


Figure 8. Normalized gate threshold voltage vs temperature

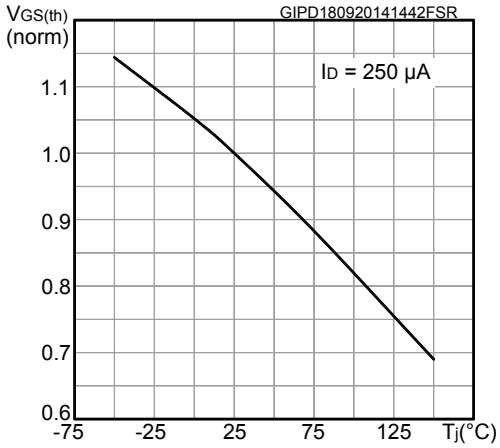


Figure 9. Normalized on-resistance vs temperature

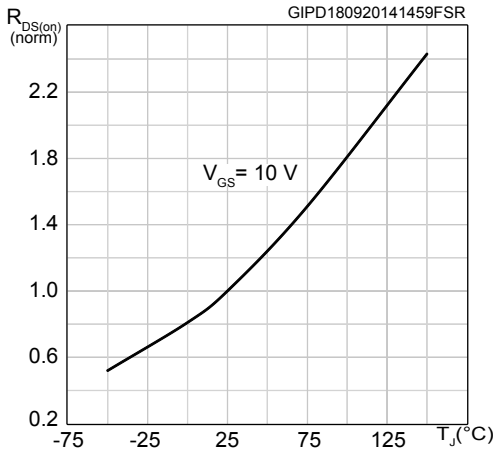


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

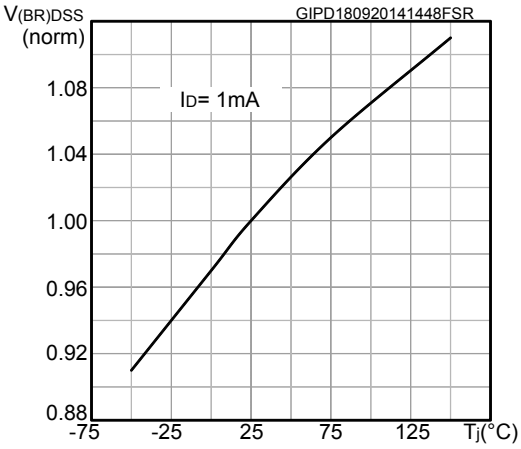


Figure 11. Source-drain diode forward characteristics

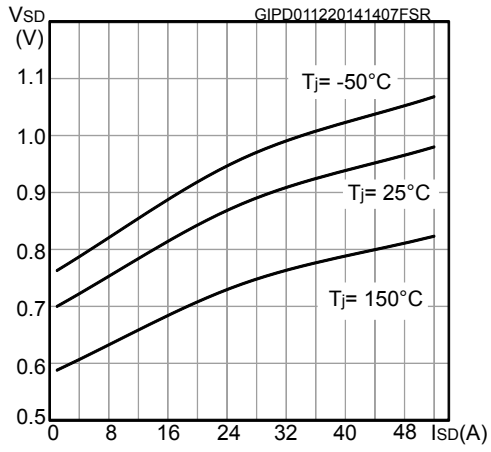
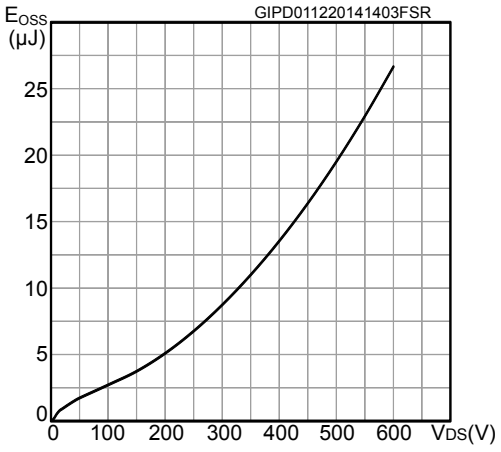


Figure 12. Output capacitance stored energy



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3 Test circuits

Figure 13. Switching times test circuit for resistive load

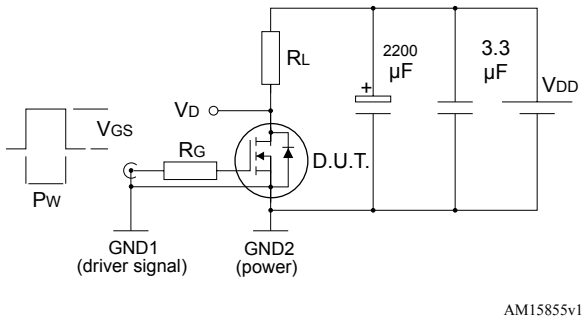


Figure 14. Test circuit for gate charge behavior

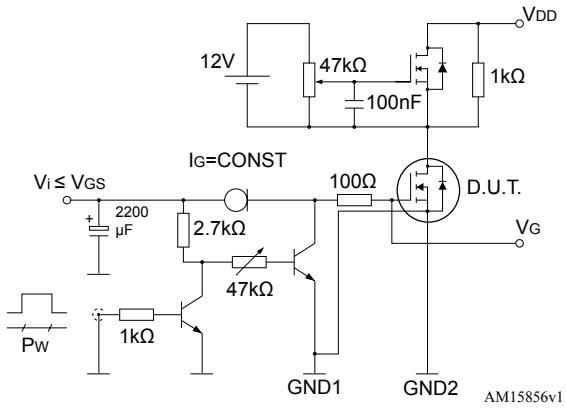


Figure 15. Test circuit for inductive load switching and diode recovery times

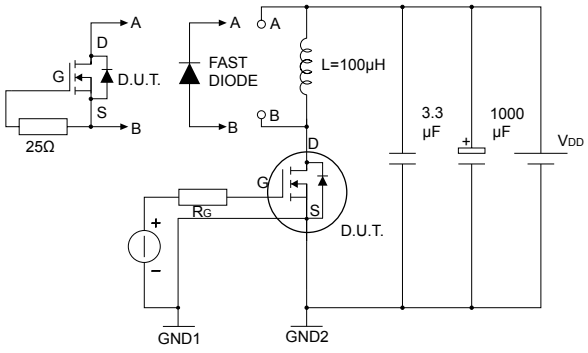


Figure 16. Unclamped inductive load test circuit

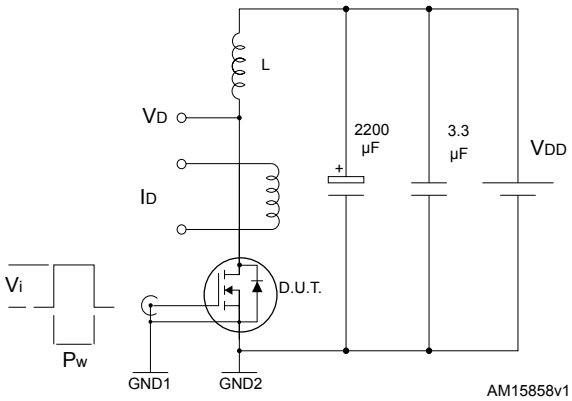


Figure 17. Unclamped inductive waveform

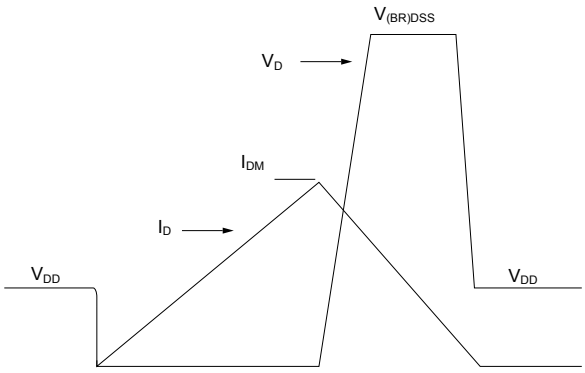
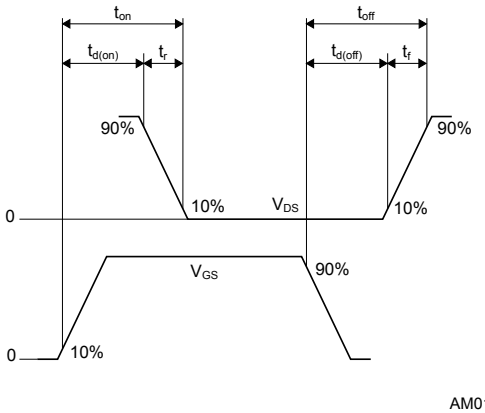


Figure 18. Switching time waveform



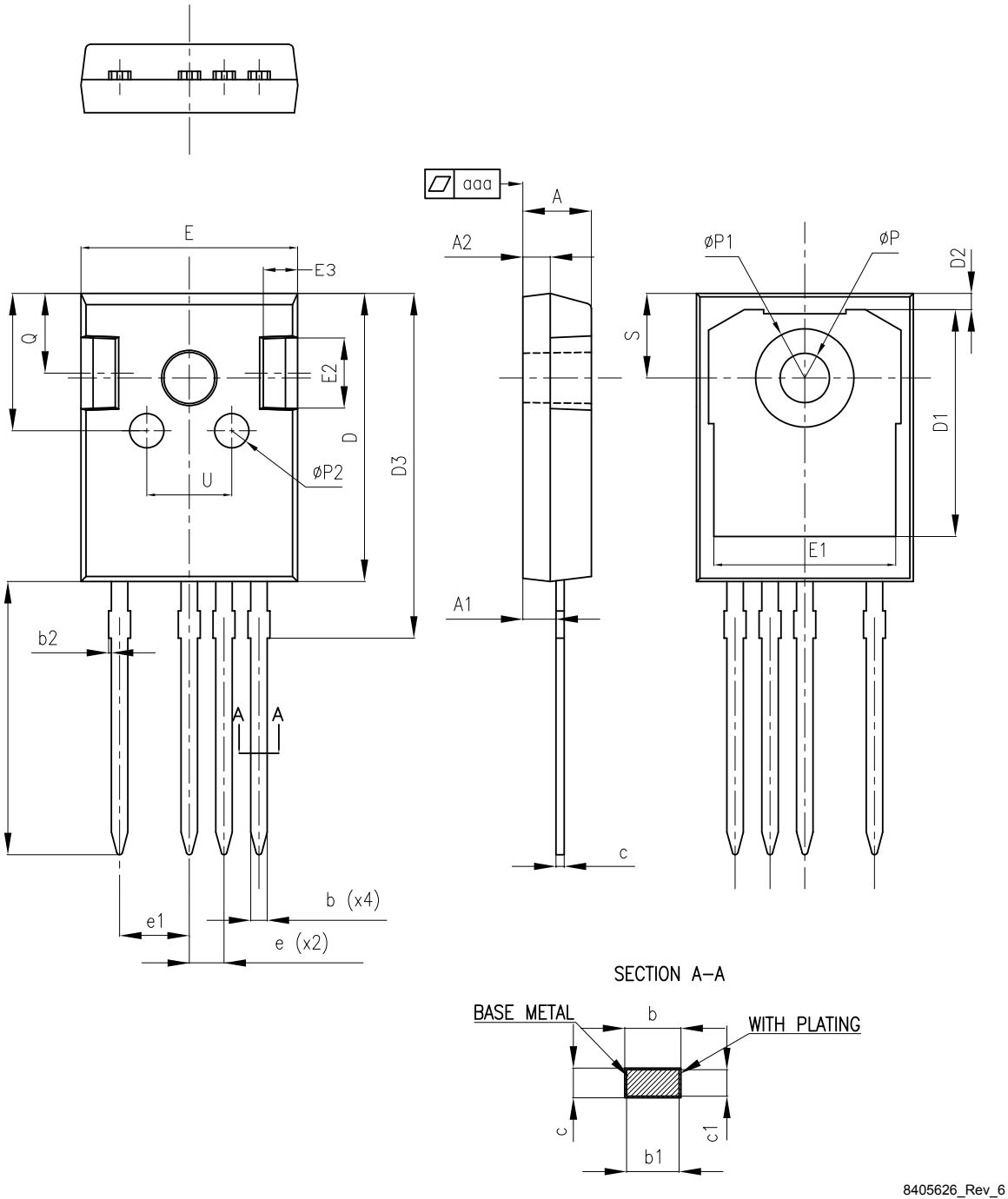
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO247-4 package information

Figure 19. TO247-4 package outline



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Table 8. **TO247-4 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0.00		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40
aaa		0.04	0.10

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Revision history

Table 9. **Document revision history**

Date	Revision	Changes
25-Jul-2014	1	Initial release.
01-Dec-2014	2	Document status promoted from preliminary to production data. Added *Section 2.1: "Electrical characteristics (curves)"*.
29-Jan-2015	3	Updated *Figure 1: "Internal schematic diagram"*.
25-Aug-2022	4	Updated *Internal schematic diagram* on cover page. Updated *Section 4 Package information*. Minor text changes.
04-Feb-2026	5	Updated Section 4.1: TO247-4 package information. Minor text changes.

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